

## PSMN6R0-30YLD

# N-channel 30 V, 6.0 m $\Omega$ logic level MOSFET in LFPAK56 using NextPowerS3 Technology

**10 February 2014** 

**Product data sheet** 

## 1. General description

Logic level gate drive N-channel enhancement mode MOSFET in LFPAK56 package. NextPowerS3 portfolio utilising Nexperia's unique "SchottkyPlus" technology delivers high efficiency, low spiking performance usually associated with MOSFETs with an integrated Schottky or Schottky-like diode but without problematic high leakage current. NextPowerS3 is particularly suited to high efficiency applications at high switching frequencies.

### 2. Features and benefits

- Ultra low Q<sub>G</sub>, Q<sub>GD</sub> and Q<sub>OSS</sub> for high system efficiency, especially at higher switching frequencies
- Superfast switching with soft-recovery; s-factor > 1
- Low spiking and ringing for low EMI designs
- Unique "SchottkyPlus" technology; Schottky-like performance with < 1 μA leakage at 25 °C
- Optimised for 4.5 V gate drive
- Low parasitic inductance and resistance
- High reliability clip bonded and solder die attach Power SO8 package; no glue, no wire bonds, gualified to 175 °C
- Wave solderable; exposed leads for optimal visual solder inspection

## 3. Applications

- On-board DC-to-DC solutions for server and telecommunications
- Secondary-side synchronous rectification in telecommunication applications
- Voltage regulator modules (VRM)
- Point-of-Load (POL) modules
- Power delivery for V-core, ASIC, DDR, GPU, VGA and system components
- Brushed and brushless motor control

### 4. Quick reference data

Table 1. Quick reference data

| Symbol           | Parameter               | Conditions   | Min | Тур | Max | Unit |
|------------------|-------------------------|--|-----|-----|-----|------|
| $V_{DS}$         | drain-source voltage    | 25 °C ≤ T <sub>j</sub> ≤ 175 °C                                | -   | -   | 30  | V    |
| I <sub>D</sub>   | drain current           | T <sub>mb</sub> = 25 °C; V <sub>GS</sub> = 10 V; <u>Fig. 2</u> | -   | -   | 66  | Α    |
| P <sub>tot</sub> | total power dissipation | T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>                         | -   | -   | 47  | W    |



### N-channel 30 V, 6.0 m $\Omega$ logic level MOSFET in LFPAK56 using **NextPowerS3 Technology**

| Symbol              | Parameter                        | Conditions  | Min | Тур | Max  | Unit |
|---------------------|----------------------------------|---|-----|-----|------|------|
| Tj                  | junction temperature             |   | -55 | -   | 175  | °C   |
| Static chara        | acteristics                      |   |     |     | '    |      |
| R <sub>DSon</sub>   | drain-source on-state resistance | $V_{GS}$ = 4.5 V; $I_D$ = 15 A; $T_j$ = 25 °C;<br>Fig. 10                                   | -   | 6.7 | 8.35 | mΩ   |
|                     |                                  | $V_{GS}$ = 10 V; $I_{D}$ = 15 A; $T_{j}$ = 25 °C;<br>Fig. 10                                | -   | 5   | 6    | mΩ   |
| Dynamic ch          | aracteristics                    |   |     |     | '    |      |
| $Q_{GD}$            | gate-drain charge                | V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 15 A; V <sub>DS</sub> = 15 V;<br>Fig. 12; Fig. 13 | -   | 1.8 | -    | nC   |
| Q <sub>G(tot)</sub> | total gate charge                | V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 15 A; V <sub>DS</sub> = 15 V;<br>Fig. 12; Fig. 13 | -   | 6.5 | -    | nC   |
| Source-drai         | in diode                         |   |     |     |      |      |
| S                   | softness factor                  | $I_S$ = 15 A; $V_{GS}$ = 0 V; $dI_S/dt$ = -100 A/ $\mu$ s; $V_{DS}$ = 15 V; Fig. 16         | -   | 1.2 | -    |      |

## **Pinning information**

Table 2. Pinning information

| 10010 21 |        |                                   |  |                |
|----------|--------|-----------------------------------|--|----------------|
| Pin      | Symbol | Description                       | Simplified outline                         | Graphic symbol |
| 1        | S      | source                            | mb   | D<br>I         |
| 2        | S      | source                            |  |                |
| 3        | S      | source                            | [d   | G T A          |
| 4        | G      | gate                              | و و و و                                    | mbb076 S       |
| mb       | D      | mounting base; connected to drain | 1 2 3 4<br>LFPAK56; Power-<br>SO8 (SOT669) |                |

## **Ordering information**

Table 3. **Ordering information** 

| Type number   | Package               |  |         |
|---------------|-----------------------|--|---------|
|               | Name                  | Description  | Version |
| PSMN6R0-30YLD | LFPAK56;<br>Power-SO8 | Plastic single-ended surface-mounted package (LFPAK56; Power-SO8); 4 leads | SOT669  |

## **Marking**

Table 4. **Marking codes** 

| Type number   |                                       | Marking code                          |   |
|---------------|---------------------------------------|---------------------------------------|---|
| PSMN6R0-30YLD |                                       | 6D030L                                |   |
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## 8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol               | Parameter                                    | Conditions   |     | Min | Max | Unit |
|----------------------|--|--|-----|-----|-----|------|
| V <sub>DS</sub>      | drain-source voltage                         | 25 °C ≤ T <sub>j</sub> ≤ 175 °C  |     | -   | 30  | V    |
| $V_{DGR}$            | drain-gate voltage                           | 25 °C ≤ $T_j$ ≤ 175 °C; $R_{GS}$ = 20 kΩ   |     | -   | 30  | V    |
| $V_{GS}$             | gate-source voltage                          |  |     | -20 | 20  | V    |
| P <sub>tot</sub>     | total power dissipation                      | T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>   |     | -   | 47  | W    |
| I <sub>D</sub>       | drain current                                | V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>   |     | -   | 66  | Α    |
|                      |  | V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 100 °C; <u>Fig. 2</u>  |     | -   | 46  | Α    |
| I <sub>DM</sub>      | peak drain current                           | pulsed; $t_p \le 10 \mu s$ ; $T_{mb} = 25 \text{ °C}$ ; Fig. 3   |     | -   | 263 | Α    |
| T <sub>stg</sub>     | storage temperature                          |  |     | -55 | 175 | °C   |
| Tj                   | junction temperature                         |  |     | -55 | 175 | °C   |
| T <sub>sld(M)</sub>  | peak soldering temperature                   |  |     | -   | 260 | °C   |
| V <sub>ESD</sub>     | electrostatic discharge voltage              | НВМ  |     | 250 | -   | V    |
| Source-dra           | in diode                                     | 1  |     |     |     |      |
| Is                   | source current                               | T <sub>mb</sub> = 25 °C  |     | -   | 39  | Α    |
| I <sub>SM</sub>      | peak source current                          | pulsed; $t_p \le 10 \mu s$ ; $T_{mb} = 25 \text{ °C}$  |     | -   | 263 | Α    |
| Avalanche            | ruggedness                                   |  |     |     | 1   |      |
| E <sub>DS(AL)S</sub> | non-repetitive drain-source avalanche energy | $V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; $I_D$ = 15 A;<br>$V_{sup} \le$ 30 V; $R_{GS}$ = 50 Ω; unclamped;<br>$t_p$ = 158 μs | [1] | -   | 46  | mJ   |

<sup>[1]</sup> Protected by 100% test

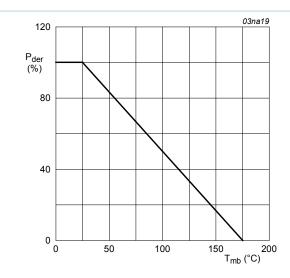


Fig. 1. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

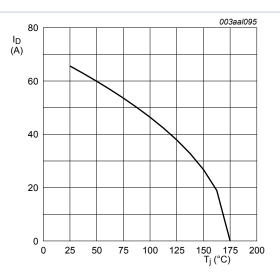


Fig. 2. Continuous drain current as a function of mounting base temperature

$$V_{GS} \ge 10V$$

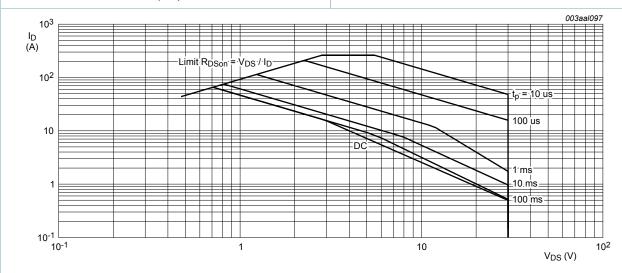


Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

 $T_{mb} = 25^{\circ}C$ ;  $I_{DM}$  is a single pulse

### 9. Thermal characteristics

Table 6. Thermal characteristics

| Symbol                | Parameter   | Conditions | Min | Тур | Max  | Unit |
|-----------------------|---|------------|-----|-----|------|------|
| R <sub>th(j-mb)</sub> | thermal resistance<br>from junction to<br>mounting base | Fig. 4     | -   | 3   | 3.22 | K/W  |

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| Symbol               | Parameter                | Conditions | Min | Тур | Max | Unit |
|----------------------|--------------------------|------------|-----|-----|-----|------|
| R <sub>th(j-a)</sub> | thermal resistance       | Fig. 5     | -   | 50  | -   | K/W  |
|                      | from junction to ambient | Fig. 6     | -   | 125 | -   | K/W  |

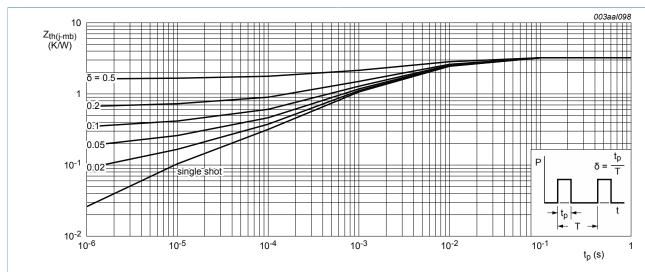


Fig. 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

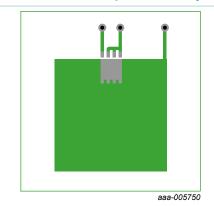


Fig. 5. PCB layout for thermal resistance junction to ambient 1" square pad; FR4 Board; 2oz copper

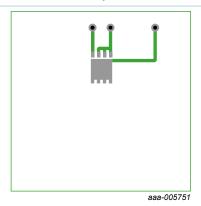


Fig. 6. PCB layout for thermal resistance junction to ambient minimum footprint; FR4 Board; 2oz copper

### 10. Characteristics

Table 7. Characteristics

| Symbol                            | Parameter                     | Conditions   | Min | Тур  | Max | Unit |
|-----------------------------------|-------------------------------|--|-----|------|-----|------|
| Static chara                      | ecteristics                   |  |     |      |     |      |
| V <sub>(BR)DSS</sub> drain-source |                               | $I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$               | 30  | -    | -   | V    |
|                                   | breakdown voltage             | $I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 °C$              | 27  | -    | -   | V    |
| $V_{GS(th)}$                      | gate-source threshold voltage | $I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$ | 1.2 | 1.83 | 2.2 | V    |

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| Symbol                           | Parameter  | Conditions  | Min | Тур  | Max  | Unit |
|----------------------------------|--|---|-----|------|------|------|
| $\Delta V_{GS(th)}\!/\!\Delta T$ | gate-source threshold voltage variation with temperature                                     | 25 °C ≤ T <sub>j</sub> ≤ 150 °C   | -   | -4   | -    | mV/K |
| I <sub>DSS</sub>                 | drain leakage current  | $V_{DS} = 24 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$                    | -   | -    | 1    | μΑ   |
|                                  |  | V <sub>DS</sub> = 24 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 150 °C                      | -   | -    | 100  | μA   |
| I <sub>GSS</sub>                 | gate leakage current   | V <sub>GS</sub> = 16 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C                       | -   | -    | 100  | nA   |
|                                  |  | V <sub>GS</sub> = -16 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C                      | -   | -    | 100  | nA   |
| R <sub>DSon</sub>                | drain-source on-state resistance   | $V_{GS} = 4.5 \text{ V}; I_D = 15 \text{ A}; T_j = 25 \text{ °C};$<br>Fig. 10               | -   | 6.7  | 8.35 | mΩ   |
|                                  | V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 15 A; T <sub>j</sub> = 150 °C;<br>Fig. 11; Fig. 10 | -   | -   | 13.8 | mΩ   |      |
|                                  | V <sub>GS</sub> = 10 V; I <sub>D</sub> = 15 A; T <sub>j</sub> = 25 °C;<br><u>Fig. 10</u>     | -   | 5   | 6    | mΩ   |      |
|                                  | $V_{GS}$ = 10 V; $I_D$ = 15 A; $T_j$ = 150 °C;<br>Fig. 11; Fig. 10                           | -   | -   | 9.9  | mΩ   |      |
| $R_G$                            | gate resistance  | f = 1 MHz   | -   | 2.36 | -    | Ω    |
| Dynamic ch                       | aracteristics  |   |     |      |      |      |
| Q <sub>G(tot)</sub>              | total gate charge  | I <sub>D</sub> = 15 A; V <sub>DS</sub> = 15 V; V <sub>GS</sub> = 10 V;<br>Fig. 12; Fig. 13  | -   | 13.7 | -    | nC   |
|                                  |  | I <sub>D</sub> = 15 A; V <sub>DS</sub> = 15 V; V <sub>GS</sub> = 4.5 V;<br>Fig. 12; Fig. 13 | -   | 6.5  | -    | nC   |
|                                  |  | I <sub>D</sub> = 0 A; V <sub>DS</sub> = 0 V; V <sub>GS</sub> = 10 V                         | -   | 12.2 | -    | nC   |
| Q <sub>GS</sub>                  | gate-source charge   | I <sub>D</sub> = 15 A; V <sub>DS</sub> = 15 V; V <sub>GS</sub> = 4.5 V;                     | -   | 1.7  | -    | nC   |
| Q <sub>GS(th)</sub>              | pre-threshold gate-<br>source charge   | Fig. 12; Fig. 13  | -   | 1.2  | -    | nC   |
| Q <sub>GS(th-pl)</sub>           | post-threshold gate-<br>source charge  |   | -   | 0.5  | -    | nC   |
| $Q_{GD}$                         | gate-drain charge  |   | -   | 1.8  | -    | nC   |
| $V_{GS(pl)}$                     | gate-source plateau voltage  | I <sub>D</sub> = 15 A; V <sub>DS</sub> = 15 V; <u>Fig. 12</u> ; <u>Fig. 13</u>              | -   | 2.2  | -    | V    |
| C <sub>iss</sub>                 | input capacitance  | V <sub>DS</sub> = 15 V; V <sub>GS</sub> = 0 V; f = 1 MHz;                                   | -   | 832  | -    | pF   |
| C <sub>oss</sub>                 | output capacitance   | T <sub>j</sub> = 25 °C; <u>Fig. 14</u>  | -   | 587  | -    | pF   |
| C <sub>rss</sub>                 | reverse transfer capacitance   |   | -   | 64   | -    | pF   |
| t <sub>d(on)</sub>               | turn-on delay time   | $V_{DS} = 15 \text{ V}; R_L = 1 \Omega; V_{GS} = 4.5 \text{ V};$                            | -   | 9    | -    | ns   |
| t <sub>r</sub>                   | rise time  | $R_{G(ext)} = 5 \Omega$   | -   | 16.2 | -    | ns   |
| t <sub>d(off)</sub>              | turn-off delay time  |   | -   | 10.5 | -    | ns   |
| t <sub>f</sub>                   | fall time  |   | _   | 10.9 | _    | ns   |

| Symbol           | Parameter                  | Conditions   |     | Min | Тур  | Max | Unit |
|------------------|----------------------------|--|-----|-----|------|-----|------|
| Q <sub>oss</sub> | output charge              | $V_{GS} = 0 \text{ V}; V_{DS} = 15 \text{ V}; f = 1 \text{ MHz};$<br>$T_j = 25 \text{ °C}$ |     | -   | 11.5 | -   | nC   |
| Source-dra       | nin diode                  |  |     |     |      |     |      |
| $V_{SD}$         | source-drain voltage       | $I_S = 10 \text{ A}$ ; $V_{GS} = 0 \text{ V}$ ; $T_j = 25 ^{\circ}\text{C}$ ; Fig. 15      |     | -   | 0.81 | 1.2 | V    |
| t <sub>rr</sub>  | reverse recovery time      | $I_S = 15 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s}; V_{GS} = 0 \text{ V};$          |     | -   | 23.4 | -   | ns   |
| Q <sub>r</sub>   | recovered charge           | V <sub>DS</sub> = 15 V; <u>Fig. 16</u>   | [1] | -   | 12.6 | -   | nC   |
| t <sub>a</sub>   | reverse recovery rise time |  |     | -   | 10.6 | -   | ns   |
| t <sub>b</sub>   | reverse recovery fall time |  |     | -   | 12.8 | -   | ns   |
| S                | softness factor            |  |     | -   | 1.2  | -   |      |

### [1] includes capacitive recovery

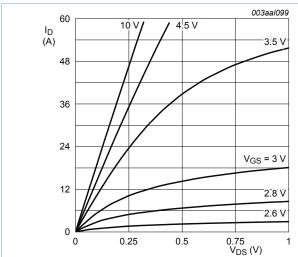


Fig. 7. Output characteristics; drain current as a function of drain-source voltage; typical values

 $T_j = 25$ °C



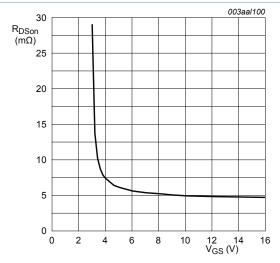


Fig. 8. Drain-source on-state resistance as a function of gate-source voltage; typical values

$$T_j = 25$$
°C;  $I_D = 15A$ 

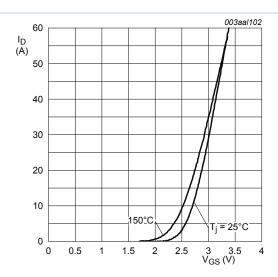
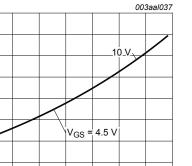


Fig. 9. Transfer characteristics; drain current as a function of gate-source voltage; typical values

 $V_{DS} = 12V$ 



120 150 T<sub>j</sub> (°C)

Fig. 11. Normalized drain-source on-state resistance factor as a function of junction temperature

$$a = \frac{R_{DSon}}{R_{DSon (25^{\circ}C)}}$$

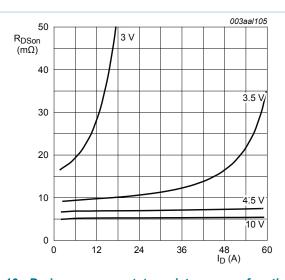


Fig. 10. Drain-source on-state resistance as a function of drain current; typical values

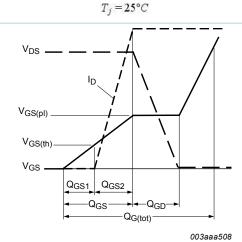


Fig. 12. Gate charge waveform definitions

1.6

1.2

0.8

0.4

-30

0 30 60

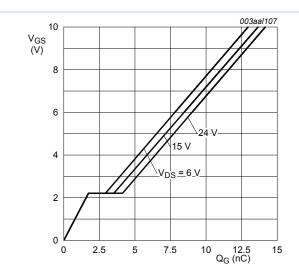


Fig. 13. Gate-source voltage as a function of gate charge; typical values

$$T_j = 25^{\circ}C; I_D = 15A$$

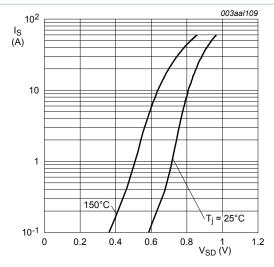


Fig. 15. Source current as a function of source-drain voltage; typical values

$$V_{GS} = 0V$$

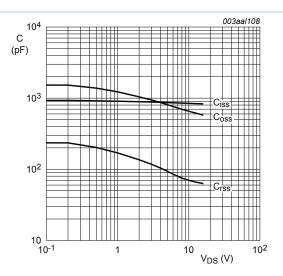


Fig. 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

$$V_{GS} = \mathbf{0}V; \ f = \mathbf{1}MHz$$

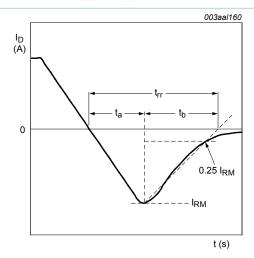
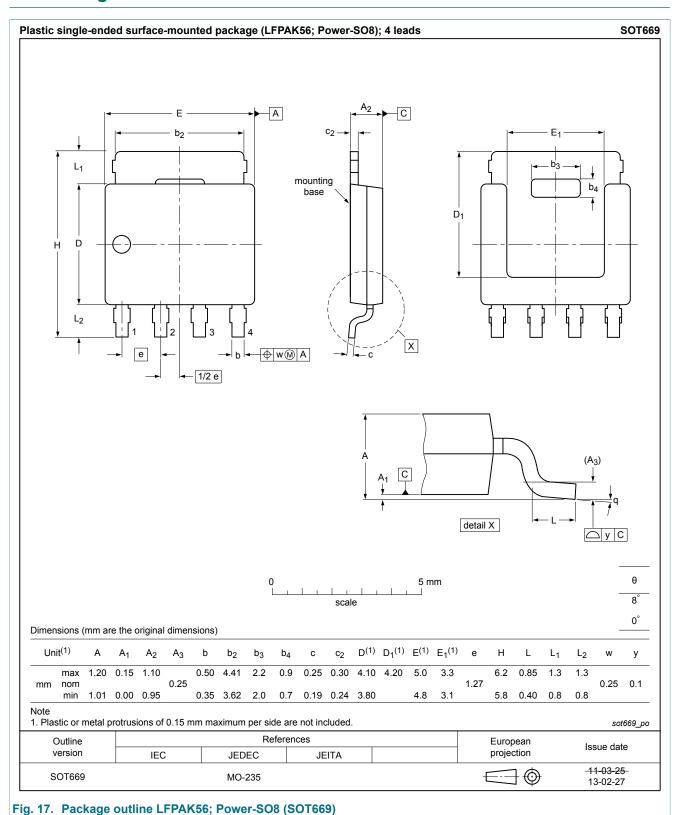


Fig. 16. Reverse recovery timing definition

## 11. Package outline



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## 12. Legal information

### 12.1 Data sheet status

| Document status [1][2]               | Product status [3] | Definition  |
|--------------------------------------|--------------------|---|
| Objective<br>[short] data<br>sheet   | Development        | This document contains data from the objective specification for product development. |
| Preliminary<br>[short] data<br>sheet | Qualification      | This document contains data from the preliminary specification.                       |
| Product<br>[short] data<br>sheet     | Production         | This document contains the product specification.                                     |

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### 13. Contents

| 1    | General description     | 1  |
|------|-------------------------|----|
| 2    | Features and benefits   | 1  |
| 3    | Applications            | 1  |
| 4    | Quick reference data    | 1  |
| 5    | Pinning information     | 2  |
| 6    | Ordering information    | 2  |
| 7    | Marking                 | 2  |
| 8    | Limiting values         | 3  |
| 9    | Thermal characteristics | 4  |
| 10   | Characteristics         | 5  |
| 11   | Package outline         | 10 |
| 12   | Legal information       | 11 |
| 12.1 | Data sheet status       | 11 |
| 12.2 | Definitions             | 11 |
| 12.3 | Disclaimers             | 11 |
| 12.4 | Trademarks              | 12 |

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